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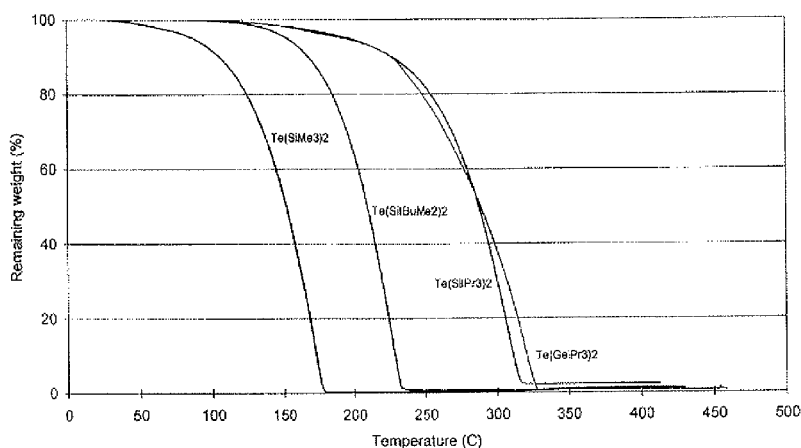


Figure 1

(57) Abstract: Methods and compositions for depositing a tellurium containing film on a substrate are disclosed. A reactor and at least one substrate disposed in the reactor are provided. A tellurium containing precursor is provided and introduced into the reactor, which is maintained at a temperature of at least 1000°C. Tellurium is deposited on to the substrate through a deposition process to form a thin film on the substrate.